

#### 20V N-Channel Enhancement Mode MOSFET - ESD Protected

Voltage 20 V Current 1.2 A

#### **Features**

- RDS(ON), VGS@4.5V, ID@1.2A<380mΩ</li>
- RDS(ON) , VGS@2.5V, ID@0.7A<680mΩ</li>
- RDS(ON), VGS@1.8V, ID@0.2A<1100mΩ(typ.)
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

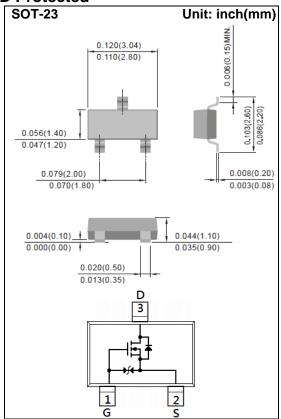
#### **Mechanical Data**

• Case: SOT-23 Package

Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0003 ounces, 0.0084 grams

Marking: A36



# **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 12	V
Continuous Drain Current		l <sub>D</sub>	1.2	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	4.8	Α
Power Dissipation	T <sub>a</sub> =25°C	_	1.25	W
	Derate above 25°C	P₀	10	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)	Reja	100	°C/W	



### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static			•				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.65	1.0	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.2A	-	310	380	mΩ	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.7A	-	440	680		
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.2A	-	700	-		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V	-	0.02	1	uA	
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 10V, V <sub>DS</sub> =0V	-	<u>+</u> 2	<u>+</u> 10	uA	
Dynamic							
Total Gate Charge	$Q_g$	101/1 401	-	0.9	-	nC	
Gate-Source Charge	Qgs	V <sub>DS</sub> =10V, I <sub>D</sub> =1.2A,	-	0.2	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V (Note 1,2)	-	0.2	-		
Input Capacitance	Ciss	101/11/101/	-	39	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	15	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	9	-		
Switching							
Turn-On Delay Time	td <sub>(on)</sub>	101111111111111111111111111111111111111	-	2.2	-		
Turn-On Rise Time	tr	V <sub>DD</sub> =10V, I <sub>D</sub> =1.2A,	-	22	-		
Turn-Off Delay Time	td <sub>(off)</sub>	V <sub>GS</sub> =4.5V,	-	9	-	ns	
Turn-Off Fall Time	tf	R <sub>G</sub> =6Ω (Note 1,2)	-	20	-		
Drain-Source Diode							
Maximum Continuous Drain-Source Diode Forward Current	Is		-	-	1.0	А	
Diode Forward Voltage	V <sub>SD</sub>	Is=1.0A, V <sub>G</sub> s=0V	-	0.93	1.3	V	

#### NOTES:

- 1. Pulse width<a></a>300us, Duty cycle<a></a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.



#### **TYPICAL CHARACTERISTIC CURVES**

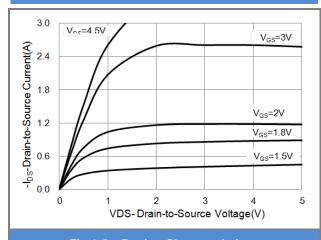
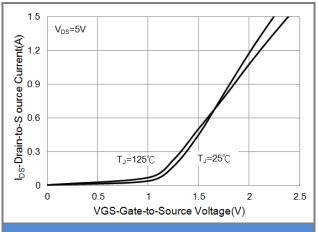


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

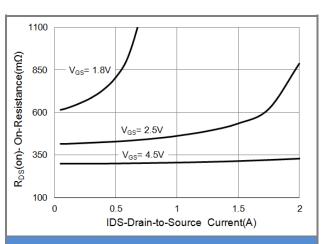


Fig.3 On-Resistance vs. Drain Current

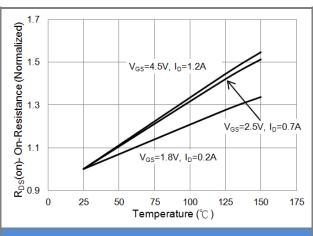
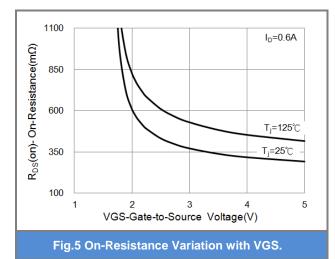
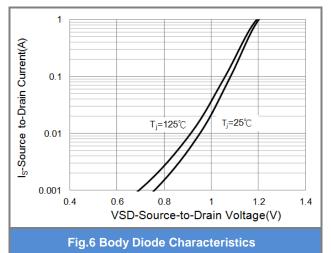


Fig.4 On-Resistance vs. Junction temperature







### **TYPICAL CHARACTERISTIC CURVES**

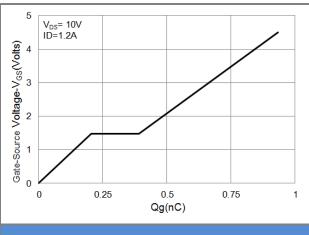


Fig.7 Gate-Charge Characteristics

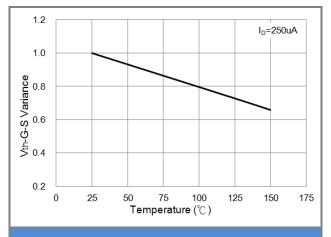


Fig.8 Threshold Voltage Variation with Temperature.

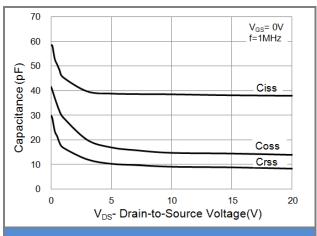


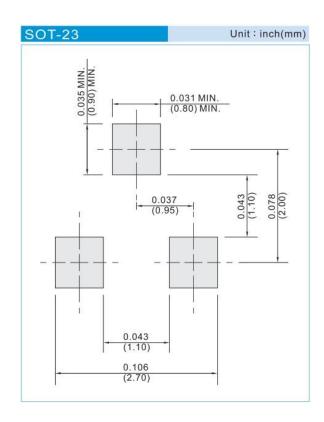
Fig.9 Threshold Voltage Variation with Temperature.



## **Product and Packing Information**

Part No.	Package Type	Packing type	Marking
PJA3436	SOT-23	3K pcs / 7" reel	A36
PJA3436	SOT-23	12K pcs / 13" reel	A36

# **Mounting Pad Layout**





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